

NSB1011XV6T5

Preferred Device

Dual Bias Resistor Transistors

NPN Silicon Surface Mount Transistors with Monolithic Bias Resistor Network

The BRT (Bias Resistor Transistor) contains a single transistor with a monolithic bias network consisting of two resistors; a series base resistor and a base-emitter resistor. These digital transistors are designed to replace a single device and its external resistor bias network. The BRT eliminates these individual components by integrating them into a single device. In the NSB1011XV6T5, two BRT devices are housed in the SOT-563 package which is ideal for low power surface mount applications where board space is at a premium.

- Simplifies Circuit Design
- Reduces Board Space
- Reduces Component Count
- This device is manufactured with a Pb-Free external lead finish only.

MAXIMUM RATINGS

(T_A = 25°C unless otherwise noted, common for Q₁ and Q₂)

| Rating | Symbol | Value | Unit |
|---------------------------|------------------|-------|------|
| Collector-Base Voltage | V _{CBO} | 50 | Vdc |
| Collector-Emitter Voltage | V _{CEO} | 50 | Vdc |
| Collector Current | I _C | 100 | mAdc |

THERMAL CHARACTERISTICS

| Characteristic (One Junction Heated) | Symbol | Max | Unit |
|--|-----------------------------------|------------------------------|-------------|
| Total Device Dissipation T _A = 25°C Derate above 25°C | P _D | 357 (Note 1) 2.9 (Note 1) | mW mW/°C |
| Thermal Resistance – Junction-to-Ambient | R _{θJA} | 350 (Note 1) | °C/W |
| Characteristic (Both Junctions Heated) | Symbol | Max | Unit |
| Total Device Dissipation T _A = 25°C Derate above 25°C | P _D | 500 (Note 1) 4.0 (Note 1) | mW mW/°C |
| Thermal Resistance – Junction-to-Ambient | R _{θJA} | 250 (Note 1) | °C/W |
| Junction and Storage Temperature Range | T _J , T _{stg} | –55 to +150 | °C |

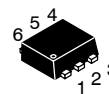
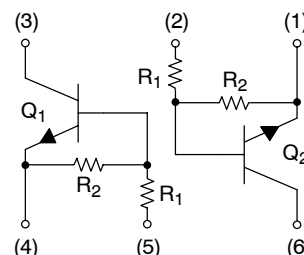
Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

1. FR-4 @ Minimum Pad.



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SOT-563
CASE 463A
PLASTIC

MARKING DIAGRAM



UT = Specific Device Code
(see table on following page)
D = Date Code

ORDERING INFORMATION

| Device | Package | Shipping† |
|--------------|----------------------|--------------------|
| NSB1011XV6T5 | SOT-563 (Pb-Free) | 8000 / Tape & Reel |

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

Preferred devices are recommended choices for future use and best overall value.

NSB1011XV6T5

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted.)

| Characteristic | Symbol | Min | Typ | Max | Unit |
|----------------|--------|-----|-----|-----|------|
|----------------|--------|-----|-----|-----|------|

Q1

OFF CHARACTERISTICS

| | | | | | |
|--|---------------|----|---|-----|------------------|
| Collector-Base Cutoff Current ($V_{CB} = 50\text{ V}$, $I_E = 0$) | I_{CBO} | – | – | 100 | nA _{dc} |
| Collector-Emitter Cutoff Current ($V_{CE} = 50\text{ V}$, $I_B = 0$) | I_{CEO} | – | – | 500 | nA _{dc} |
| Emitter-Base Cutoff Current ($V_{EB} = 6.0\text{ V}$, $I_C = 0$) | I_{EBO} | – | – | 0.5 | mA _{dc} |
| Collector-Base Breakdown Voltage ($I_C = 10\text{ }\mu\text{A}$, $I_E = 0$) | $V_{(BR)CBO}$ | 50 | – | – | V _{dc} |
| Collector-Emitter Breakdown Voltage (Note 2) ($I_C = 2.0\text{ mA}$, $I_B = 0$) | $V_{(BR)CEO}$ | 50 | – | – | V _{dc} |

ON CHARACTERISTICS (Note 2)

| | | | | | |
|--|---------------|-----|-----|------|-----------------|
| DC Current Gain ($V_{CE} = 10\text{ V}$, $I_C = 5.0\text{ mA}$) | h_{FE} | 35 | 60 | – | – |
| Collector-Emitter Saturation Voltage ($I_C = 10\text{ mA}$, $I_B = 0.3\text{ mA}$) | $V_{CE(sat)}$ | – | – | 0.25 | V _{dc} |
| Output Voltage (on) ($V_{CC} = 5.0\text{ V}$, $V_B = 2.5\text{ V}$, $R_L = 1.0\text{ k}\Omega$) | V_{OL} | – | – | 0.2 | V _{dc} |
| Output Voltage (off) ($V_{CC} = 5.0\text{ V}$, $V_B = 0.5\text{ V}$, $R_L = 1.0\text{ k}\Omega$) | V_{OH} | 4.9 | – | – | V _{dc} |
| Input Resistor | R_1 | 7.0 | 10 | 13 | k Ω |
| Resistor Ratio | R_1/R_2 | 0.8 | 1.0 | 1.2 | – |

Q2

OFF CHARACTERISTICS

| | | | | | |
|--|---------------|----|---|-----|------------------|
| Collector-Base Cutoff Current ($V_{CB} = 50\text{ V}$, $I_E = 0$) | I_{CBO} | – | – | 100 | nA _{dc} |
| Collector-Emitter Cutoff Current ($V_{CE} = 50\text{ V}$, $I_B = 0$) | I_{CEO} | – | – | 500 | nA _{dc} |
| Emitter-Base Cutoff Current ($V_{EB} = 6.0\text{ V}$, $I_C = 0$) | I_{EBO} | – | – | 0.2 | mA _{dc} |
| Collector-Base Breakdown Voltage ($I_C = 10\text{ }\mu\text{A}$, $I_E = 0$) | $V_{(BR)CBO}$ | 50 | – | – | V _{dc} |
| Collector-Emitter Breakdown Voltage (Note 2) ($I_C = 2.0\text{ mA}$, $I_B = 0$) | $V_{(BR)CEO}$ | 50 | – | – | V _{dc} |

ON CHARACTERISTICS (Note 2)

| | | | | | |
|--|---------------|-------|-------|-------|-----------------|
| DC Current Gain ($V_{CE} = 10\text{ V}$, $I_C = 5.0\text{ mA}$) | h_{FE} | 80 | 140 | – | – |
| Collector-Emitter Saturation Voltage ($I_C = 10\text{ mA}$, $I_B = 0.3\text{ mA}$) | $V_{CE(sat)}$ | – | – | 0.25 | V _{dc} |
| Output Voltage (on) ($V_{CC} = 5.0\text{ V}$, $V_B = 2.5\text{ V}$, $R_L = 1.0\text{ k}\Omega$) | V_{OL} | – | – | 0.2 | V _{dc} |
| Output Voltage (off) ($V_{CC} = 5.0\text{ V}$, $V_B = 0.5\text{ V}$, $R_L = 1.0\text{ k}\Omega$) | V_{OH} | 4.9 | – | – | V _{dc} |
| Input Resistor | R_1 | 1.54 | 2.2 | 2.86 | k Ω |
| Resistor Ratio | R_1/R_2 | 0.038 | 0.047 | 0.056 | – |

2. Pulse Test: Pulse Width < 300 μs , Duty Cycle < 2.0%.

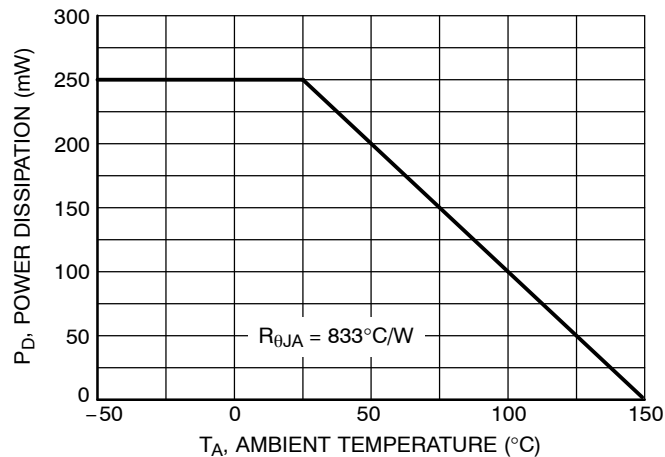


Figure 1. Derating Curve

TYPICAL ELECTRICAL CHARACTERISTICS — Q1

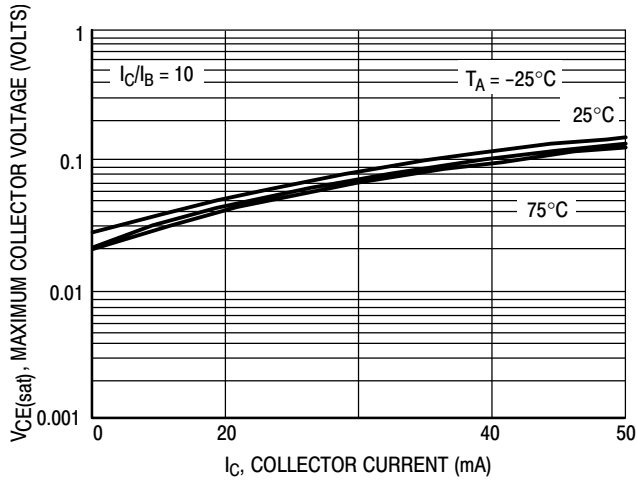


Figure 2. $V_{CE(sat)}$ versus I_C

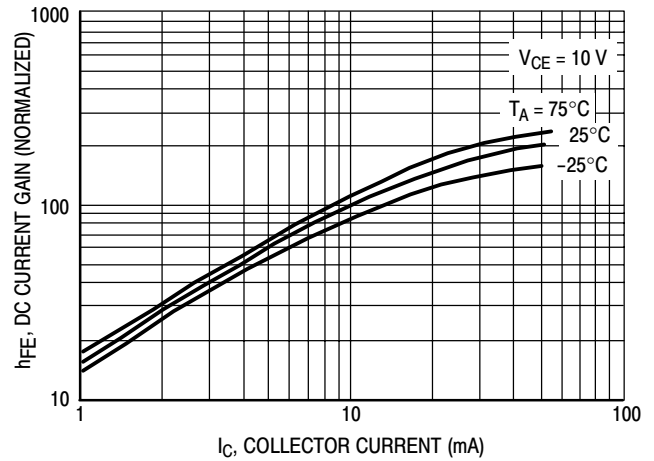


Figure 3. DC Current Gain

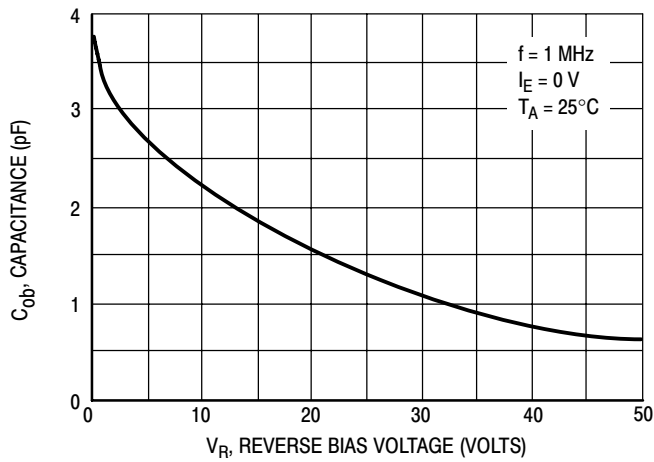


Figure 4. Output Capacitance

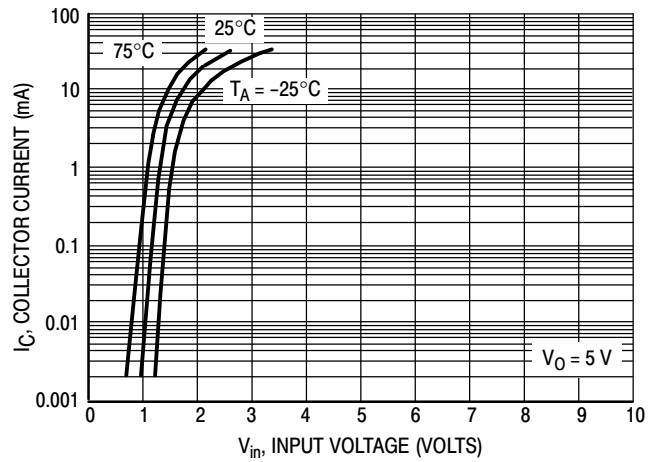


Figure 5. Output Current versus Input Voltage

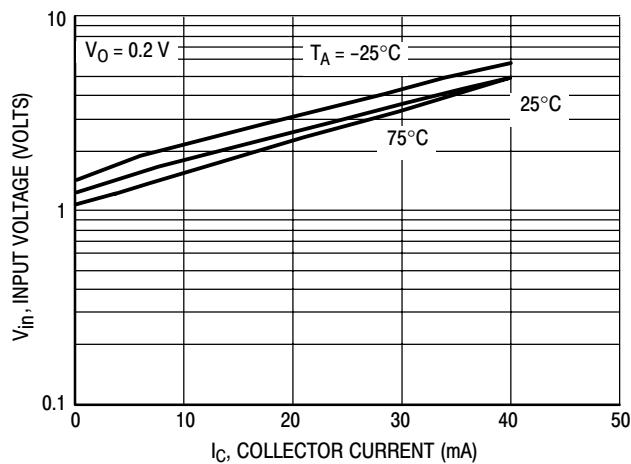


Figure 6. Input Voltage versus Output Current

TYPICAL ELECTRICAL CHARACTERISTICS — Q2

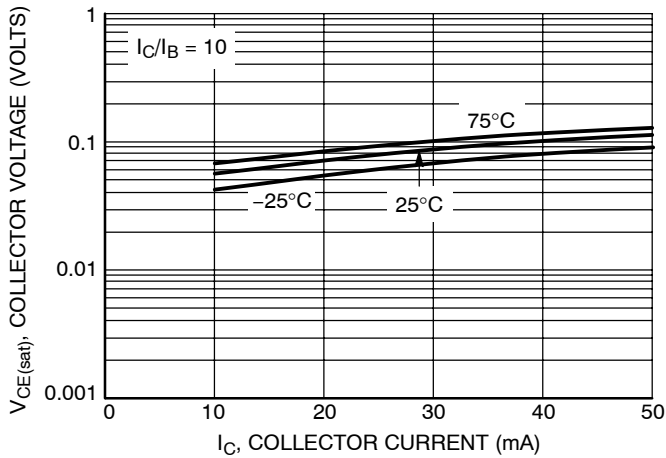


Figure 7. $V_{CE(sat)}$ versus I_C

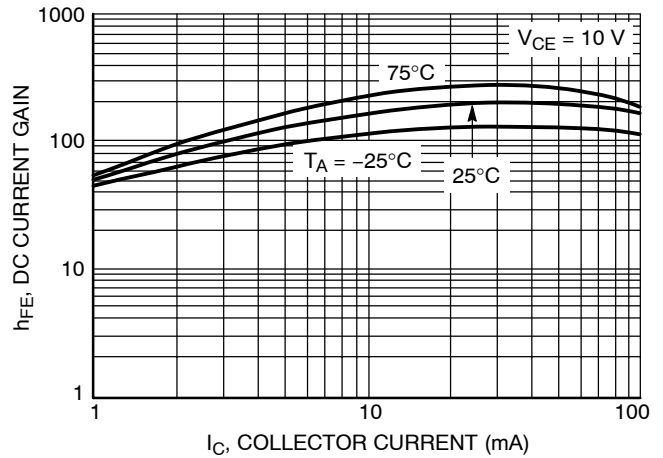


Figure 8. DC Current Gain

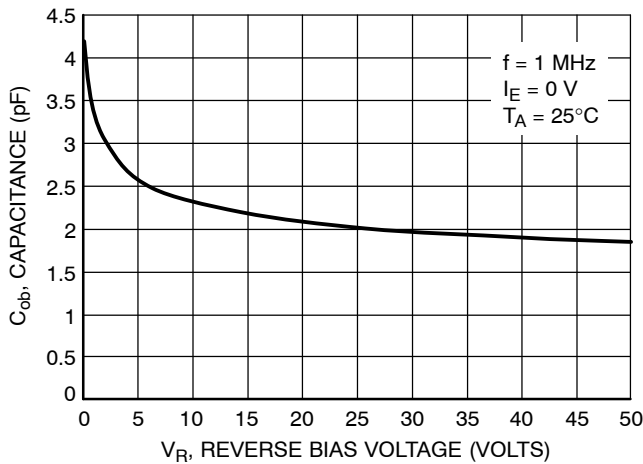


Figure 9. Output Capacitance

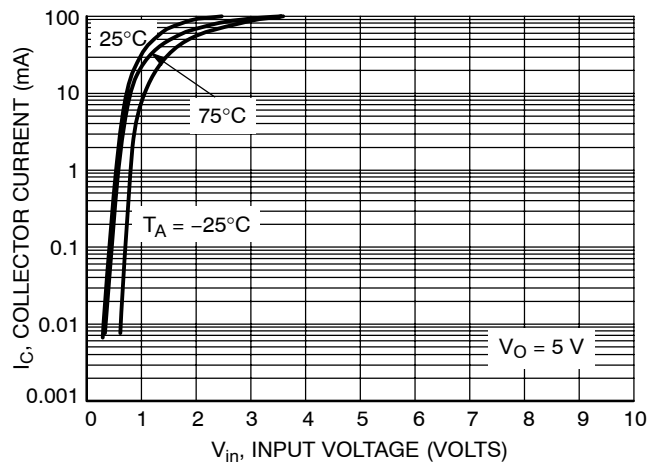


Figure 10. Output Current versus Input Voltage

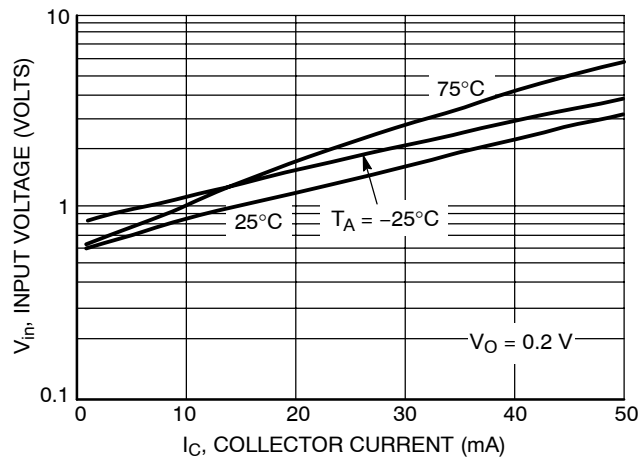
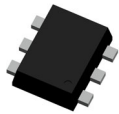


Figure 11. Input Voltage versus Output Current

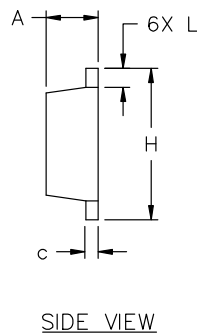
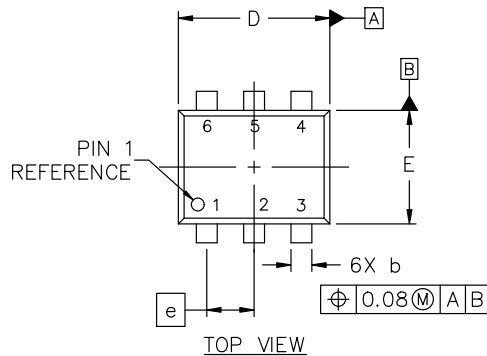


SOT-563-6 1.60x1.20x0.55, 0.50P
CASE 463A
ISSUE J

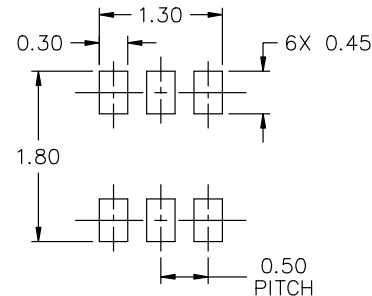
DATE 15 FEB 2024

NOTES:

1. DIMENSIONING AND TOLERANCING CONFORM TO ASME Y14.5-2018.
2. ALL DIMENSION ARE IN MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.



| DIM | MILLIMETERS | | |
|-----|-------------|------|------|
| | MIN. | NOM. | MAX. |
| A | 0.50 | 0.55 | 0.60 |
| b | 0.17 | 0.22 | 0.27 |
| c | 0.08 | 0.13 | 0.18 |
| D | 1.50 | 1.60 | 1.70 |
| E | 1.10 | 1.20 | 1.30 |
| e | 0.50 BSC | | |
| H | 1.50 | 1.60 | 1.70 |
| L | 0.10 | 0.20 | 0.30 |



RECOMMENDED MOUNTING FOOTPRINT*

* FOR ADDITIONAL INFORMATION ON OUR Pb-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ON SEMICONDUCTOR SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERM/D.

STYLE 1:
PIN 1. EMITTER 1
2. BASE 1
3. COLLECTOR 2
4. EMITTER 2
5. BASE 2
6. COLLECTOR 1

STYLE 2:
PIN 1. EMITTER 1
2. EMITTER 2
3. BASE 2
4. COLLECTOR 2
5. BASE 1
6. COLLECTOR 1

STYLE 3:
PIN 1. CATHODE 1
2. CATHODE 1
3. ANODE/ANODE 2
4. CATHODE 2
5. CATHODE 2
6. ANODE/ANODE 1

STYLE 4:
PIN 1. COLLECTOR
2. COLLECTOR
3. BASE
4. EMITTER
5. COLLECTOR
6. COLLECTOR

STYLE 5:
PIN 1. CATHODE
2. CATHODE
3. ANODE
4. ANODE
5. CATHODE
6. CATHODE

STYLE 6:
PIN 1. CATHODE
2. ANODE
3. CATHODE
4. CATHODE
5. CATHODE
6. CATHODE

STYLE 7:
PIN 1. CATHODE
2. ANODE
3. CATHODE
4. CATHODE
5. ANODE
6. CATHODE

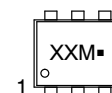
STYLE 8:
PIN 1. DRAIN
2. DRAIN
3. GATE
4. SOURCE
5. DRAIN
6. DRAIN

STYLE 9:
PIN 1. SOURCE 1
2. GATE 1
3. DRAIN 2
4. SOURCE 2
5. GATE 2
6. DRAIN 1

STYLE 10:
PIN 1. CATHODE 1
2. N/C
3. CATHODE 2
4. ANODE 2
5. N/C
6. ANODE 1

STYLE 11:
PIN 1. EMITTER 2
2. BASE 2
3. COLLECTOR 1
4. EMITTER 1
5. BASE 1
6. COLLECTOR 2

**GENERIC
MARKING DIAGRAM***



XX = Specific Device Code
M = Month Code
▪ = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

| | | |
|-------------------------|--|--|
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| DESCRIPTION: | SOT-563-6 1.60x1.20x0.55, 0.50P | PAGE 1 OF 1 |

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